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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z4d
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	177
Program Memory Size	3MB (3M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 33x10b, 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-LQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc564b74l8c9e0x

List of figures

1 Introduction

1.1 Document Overview

This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the SPC564Bxx and SPC56ECxx device. To ensure a complete understanding of the device functionality, refer also to the SPC564Bxx and SPC56ECxx Reference Manual.

1.2 Description

The SPC564Bxx and SPC56ECxx is a new family of next generation microcontrollers built on the Power Architecture embedded category. This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the device.

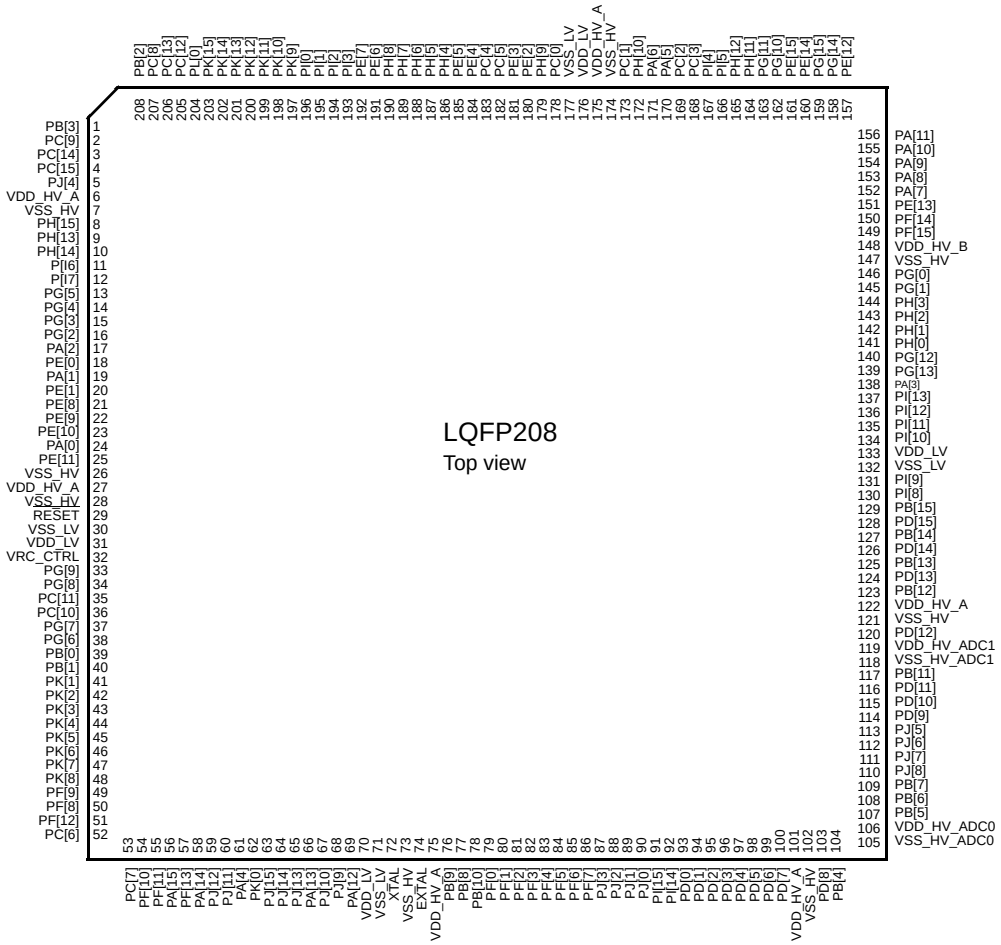
The SPC564Bxx and SPC56ECxx family expands the range of the SPC560B microcontroller family. It provides the scalability needed to implement platform approaches and delivers the performance required by increasingly sophisticated software architectures. The advanced and cost-efficient host processor core of the SPC564Bxx and SPC56ECxx automotive controller family complies with the Power Architecture embedded category, which is 100 percent user-mode compatible with the original Power Architecture user instruction set architecture (UISA). It operates at speeds of up to 120 MHz and offers high performance processing optimized for low power consumption. It also capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

Table 2. SPC564Bxx and SPC56ECxx family comparison[1] (continued)

Feature	SPC564B64		SPC56EC64			SPC564B70		SPC56EC70			SPC564B74		SPC56EC74		
Package	LQFP 176	LQFP 208	LQFP 176	LQFP 208	LBGA 256	LQFP 176	LQFP 208	LQFP 176	LQFP 208	LBGA 256	LQFP 176	LQFP 208	LQFP 176	LQFP 208	LBGA 256
FlexRay	Yes														
STCU[11]	Yes														
Ethernet	No		Yes			No		Yes			No		Yes		
I^2C	1														
32 kHz oscillator (SXOSC)	Yes														
GPIO[12]	147	177	147	177	199	147	177	147	177	199	147	177	147	177	199
Debug	JTAG				Nexus 3+	JTAG				Nexus 3+	JTAG				Nexus 3+
Cryptographic Services Engine (CSE)	Optional														

1. Feature set dependent on selected peripheral multiplexing; table shows example.
2. Based on 125 °C ambient operating temperature and subject to full device characterization.
3. The e200z0h can run at speeds up to 80 MHz. However, if system frequency is >80 MHz (e.g., e200z4d running at 120 MHz) the e200z0h needs to run at 1/2 system frequency. There is a configurable e200z0 system clock divider for this purpose.
4. DMAMUX also included that allows for software selection of 32 out of a possible 57 sources.
5. Not shared with 12-bit ADC, but possibly shared with other alternate functions.
6. There are 23 dedicated ANS plus 4 dedicated ANX channels on LQPF176. For higher pin count packages, there are 29 dedicated ANS plus 4 dedicated ANX channels.
7. 16x precision channels (ANP) and 3x standard (ANS).
8. Not shared with 10-bit ADC, but possibly shared with other alternate functions.
9. As a minimum, all timer channels can function as PWM or Input Capture and Output Control. Refer to the eMIOS section of the device reference manual for information on the channel configuration and functions.
10. CAN Sampler also included that allows ID of CAN message to be captured when in low power mode.
11. STCU controls MBIST activation and reporting.
12. Estimated I/O count for proposed packages based on multiplexing with peripherals.

Figure 3. 208-pin LQFP configuration



NOTE
1) VDD_HV_B supplies the IO voltage domain for the pins PE[12], PA[11], PA[10], PA[9], PA[8], PA[7], PE[13], PF[14], PF[15], PG[0], PG[1], PH[3], PH[2], PH[1], PH[0], PG[12], PG[13], and PA[3].
2) Availability of port pin alternate functions depends on product selection.

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 — —	GPI[51] — — — ADC0_P[7] ADC1_P[7]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	80	96	R13
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 — —	GPI[52] — — — ADC0_P[8] ADC1_P[8]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	81	97	P12
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 — —	GPI[53] — — — ADC0_P[9] ADC1_P[9]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	82	98	T14
PD[6]	PCR[54]	AF0 AF1 AF2 AF3 — —	GPI[54] — — — ADC0_P[10] ADC1_P[10]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	83	99	R14
PD[7]	PCR[55]	AF0 AF1 AF2 AF3 — —	GPI[55] — — — ADC0_P[11] ADC1_P[11]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	84	100	P13
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 — —	GPI[56] — — — ADC0_P[12] ADC1_P[12]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	87	103	P14

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								LQFP 176	LQFP 208	LBGA256
PL[14]	PCR[190]	AF0 AF1 AF2 AF3	GPIO[190] — MDO7 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E12
PL[15]	PCR[191]	AF0 AF1 AF2 AF3	GPIO[191] — MDO8 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E11
PM[0]	PCR[192]	AF0 AF1 AF2 AF3	GPIO[192] — MDO9 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E10
PM[1]	PCR[193]	AF0 AF1 AF2 AF3	GPIO[193] — MDO10 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	E9
PM[2]	PCR[194]	AF0 AF1 AF2 AF3	GPIO[194] — MDO11 —	SIUL — Nexus —	I/O — O —	M/S	Tristate	—	—	F12
PM[3]	PCR[195]	AF0 AF1 AF2 AF3	GPIO[195] — — —	SIUL — — —	I/O — — —	M/S	Tristate	—	—	K12
PM[4]	PCR[196]	AF0 AF1 AF2 AF3	GPIO[196] — — —	SIUL — — —	I/O — — —	M/S	Tristate	—	—	L12

Table 9. Absolute maximum ratings (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{RC_CTRL} (2)		Base control voltage for external BCP68 NPN device	Relative to V_{DD_LV}	0	V_{DD_LV} + 1	V
V_{SS_ADC}	S R	Voltage on VSS_HV_ADC0, VSS_HV_ADC1 (ADC reference) pin with respect to ground (V_{SS_HV})	—	V_{SS_HV} – 0.1	V_{SS_HV} + 0.1	V
$V_{DD\_HV\_ADC0}$	S R	Voltage on VDD_HV_ADC0 with respect to ground (V_{SS_HV})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_A}$ (3)	$V_{DD\_HV\_A}$ – 0.3	$V_{DD\_HV\_A}$+0.3	
$V_{DD\_HV\_ADC1}$ (4)	S R	Voltage on VDD_HV_ADC1 with respect to ground (V_{SS_HV})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_A}$ 2	$V_{DD\_HV\_A}$–0.3	$V_{DD\_HV\_A}$+0.3	
V_{IN}	S R	Voltage on any GPIO pin with respect to ground (V_{SS_HV})	Relative to $V_{DD\_HV\_A/HV\_B}$	$V_{DD\_HV\_A/HV\_B}$– 0.3	$V_{DD\_HV\_A/HV\_B}$+ 0.3	V
I_{INJPAD}	S R	Injected input current on any pin during overload condition	—	–10	10	mA
I_{INJSUM}	S R	Absolute sum of all injected input currents during overload condition	—	–50	50	
I_{AVGSEG} (5)	S R	Sum of all the static I/O current within a supply segment ($V_{DD\_HV\_A}$ or $V_{DD\_HV\_B}$)	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0		70	mA
			V_{DD} = 3.3 V ± 10%, PAD3V5V = 1		64	
$T_{STORAGE}$	S R	Storage temperature	—	–55 (6)	150	°C

1. $V_{DD\_HV\_B}$ can be independently controlled from $V_{DD\_HV\_A}$. These can ramp up or ramp down in any order. Design is robust against any supply order.
2. This voltage is internally generated by the device and no external voltage should be supplied.
3. Both the relative and the fixed conditions must be met. For instance: If $V_{DD\_HV\_A}$ is 5.9 V, $V_{DD\_HV\_ADC0}$ maximum value is 6.0 V then, despite the relative condition, the max value is $V_{DD\_HV\_A}$ + 0.3 = 6.2 V.
4. PA3, PA7, PA10, PA11 and PE12 ADC_1 channels are coming from $V_{DD\_HV\_B}$ domain hence $V_{DD\_HV\_ADC1}$ should be within ±300 mV of $V_{DD\_HV\_B}$ when these channels are used for ADC_1.
5. Any temperature beyond 125 °C should limit the current to 50 mA (max).
6. This is the storage temperature for the flash memory.

Note: Stresses exceeding the recommended absolute maximum ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. During overload conditions (V_{IN} > $V_{DD\_HV\_A/HV\_B}$ or V_{IN} < V_{SS_HV}), the voltage on pins with respect to ground (V_{SS_HV}) must not exceed the recommended values.

Table 11. Recommended operating conditions (5.0 V) (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
$V_{DD\_HV\_ADC0}$ (5)	SR	Voltage on VDD_HV_ADC0 with respect to ground (V_{SS_HV})	—	4.5	5.5	V
			Voltage drop(2)	3.0	5.5	
			Relative to $V_{DD\_HV\_A}$(6)	$V_{DD\_HV\_A}$ – 0.1	$V_{DD\_HV\_A}$ + 0.1	
$V_{DD\_HV\_ADC1}$ (7)	SR	Voltage on VDD_HV_ADC1 with respect to ground (V_{SS_HV})	—	4.5	5.5	V
			Voltage drop(2)	3.0	5.5	
			Relative to $V_{DD\_HV\_A}$(6)	$V_{DD\_HV\_A}$ – 0.1	$V_{DD\_HV\_A}$ + 0.1	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS_HV})	—	V_{SS_HV} –0.1	—	V
			Relative to $V_{DD\_HV\_A/HV\_B}$	—	$V_{DD\_HV\_A/HV\_B}$ + 0.1	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
TV_{DD}	SR	$V_{DD\_HV\_A}$ slope to ensure correct power up(8)	—	—	0.5	V/µs
			—	0.5	—	V/min
T_{A} C-Grade Part	SR	Ambient temperature under bias	—	–40	85	°C
T_{J} C-Grade Part	SR	Junction temperature under bias	—	–40	110	
T_{A} V-Grade Part	SR	Ambient temperature under bias	—	–40	105	
T_{J} V-Grade Part	SR	Junction temperature under bias	—	–40	130	
T_{A} M-Grade Part	SR	Ambient temperature under bias	—	–40	125	
T_{J} M-Grade Part	SR	Junction temperature under bias	—	–40	150	

1. 100 nF EMI capacitance need to be provided between each VDD/VSS_HV pair.
2. Full device operation is guaranteed by design from 3.0 V–5.5 V. OSC functionality is guaranteed from the entire range 3.0V–5.5 V, the parametrics measured are at 3.0V and 5.5V (extreme voltage ranges to cover the range of operation). The parametrics might have some variation in the intermediate voltage range, but there is no impact to functionality.
3. 100 nF EMI capacitance needs to be provided between each VDD_LV/VSS_LV supply pair. 10 µF bulk capacitance needs to be provided as CREG on each VDD_LV pin.
4. This voltage is internally generated by the device and no external voltage should be supplied.
5. 100 nF capacitance needs to be provided between $V_{DD\_HV\_(ADC0/ADC1)}$/$V_{SS\_HV\_(ADC0/ADC1)}$ pair.
6. Both the relative and the fixed conditions must be met. For instance: If $V_{DD\_HV\_A}$ is 5.9 V, $V_{DD\_HV\_ADC0}$ maximum value is 6.0 V then, despite the relative condition, the max value is $V_{DD\_HV\_A}$ + 0.3 = 6.2 V.
7. PA3, PA7, PA10, PA11 and PE12 ADC_1 channels are coming from $V_{DD\_HV\_B}$ domain hence VDD_HV_ADC1 should be within ±100 mV of $V_{DD\_HV\_B}$ when these channels are used for ADC_1.

Table 21. I/O consumption

Symbol		C	Parameter	Conditions[1],[2]		Value[3]			Unit
						Min	Typ	Max	
I_{SWTSLW}[4]	CC	D	Peak I/O current for SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	19.9	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	15.5	
I_{SWTMED}[4]	CC	D	Peak I/O current for MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	28.8	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	16.3	
I_{SWTFST}[4]	CC	D	Peak I/O current for FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	113.5	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	52.1	
I_{RMSSLW}	CC	D	Root mean square I/O current for SLOW configuration	C_L = 25 pF, 2 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	2.22	mA
				C_L = 25 pF, 4 MHz		—	—	3.13	
				C_L = 100 pF, 2 MHz		—	—	6.54	
				C_L = 25 pF, 2 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	1.51	
				C_L = 25 pF, 4 MHz		—	—	2.14	
				C_L = 100 pF, 2 MHz		—	—	4.33	
I_{RMSMED}	CC	D	Root mean square I/O current for MEDIUM configuration	C_L = 25 pF, 13 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	6.5	mA
				C_L = 25 pF, 40 MHz		—	—	13.32	
				C_L = 100 pF, 13 MHz		—	—	18.26	
				C_L = 25 pF, 13 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	4.91	
				C_L = 25 pF, 40 MHz		—	—	8.47	
				C_L = 100 pF, 13 MHz		—	—	10.94	
I_{RMSFST}	CC	D	Root mean square I/O current for FAST configuration	C_L = 25 pF, 40 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	21.05	mA
				C_L = 25 pF, 64 MHz		—	—	33	
				C_L = 100 pF, 40 MHz		—	—	55.77	
				C_L = 25 pF, 40 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	14	
				C_L = 25 pF, 64 MHz		—	—	20	
				C_L = 100 pF, 40 MHz		—	—	34.89	
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0		—	—	70	mA
				V_{DD} = 3.3 V ± 10%, PAD3V5V = 1		—	—	65[4]	

1. V_{DD} = 3.3 V ± 10 % / 5.0 V ± 10 %, T_A = –40 to 125 °C, unless otherwise specified.
2. V_{DD} as mentioned in the table is $V_{DD\_HV\_A}$/$V_{DD\_HV\_B}$.
3. All values need to be confirmed during device validation.
4. Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

Figure 9. Low voltage monitor vs. Reset

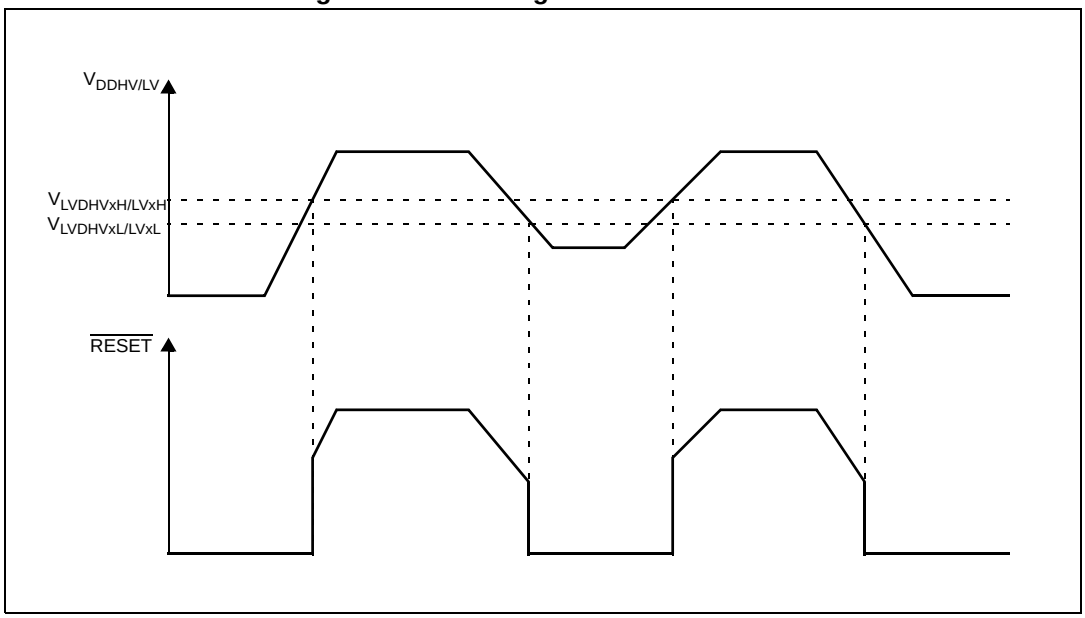


Table 24. Low voltage monitor electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
V_{PORUP}	SR	P	Supply for functional POR module	—	1.0	—	5.5	V
V_{PORH}	CC	P	Power-on reset threshold	—	1.5	—	2.6	
$V_{LVDHV3H}$	CC	T	LVDHV3 low voltage detector high threshold	—	2.7	—	2.85	
$V_{LVDHV3L}$	CC	T	LVDHV3 low voltage detector low threshold	—	2.6	—	2.74	
$V_{LVDHV5H}$	CC	T	LVDHV5 low voltage detector high threshold	—	4.3	—	4.5	
$V_{LVDHV5L}$	CC	T	LVDHV5 low voltage detector low threshold	—	4.2	—	4.4	
$V_{LVDLVCORL}$	CC	P	LVDLVCOR low voltage detector low threshold	T_A = 25 °C, after trimming	1.08	—	1.17	
$V_{LVDLVBKPL}$	CC	P	LVDLVBKP low voltage detector low threshold		1.08	—	1.17	

1. V_{DD} = 3.3 V ± 10 % / 5.0 V ± 10 %, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.

3.9 Low voltage domain power consumption

Table 25 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

Table 27. Data flash memory—Program and erase specifications

Symbol		C	Parameter	Value				Unit
				Min	Typ(1)	Initial max(2)	Max(3)	
$T_{wprogram}$	CC	C	Word (32 bits) program time(4)	—	30	70	500	µs
$T_{16Kpperase}$			16 KB block pre-program and erase time	—	700	800	5000	ms
T_{eslat}		D	Erase Suspend Latency	—	—	30	30	µs
t_{ESRT}(5)		C	Erase Suspend Request Rate	10	—	—	—	ms
t_{PABT}		D	Program Abort Latency	—	—	12	12	µs
t_{EAPT}		D	Erase Abort Latency	—	—	30	30	µs

1. Typical program and erase times assume nominal supply values and operation at 25 °C. All times are subject to change pending device characterization.
2. Initial factory condition: < 100 program/erase cycles, 25 °C, typical supply voltage.
3. The maximum program and erase times occur after the specified number of program/erase cycles. These maximum values are characterized but not guaranteed.
4. Actual hardware programming times. This does not include software overhead.
5. It is time between erase suspend resume and next erase suspend.

Table 28. Flash memory module life

Symbol		C	Parameter	Conditions	Value		Unit
					Min	Typ	
P/E	CC	C	Number of program/erase cycles per block for 16 Kbyte blocks over the operating temperature range (T_J)	—	100000	100000	cycles
			Number of program/erase cycles per block for 32 Kbyte blocks over the operating temperature range (T_J)	—	10000	100000	cycles
			Number of program/erase cycles per block for 128 Kbyte blocks over the operating temperature range (T_J)	—	1000	100000	cycles
Retention	CC	C	Minimum data retention at 85 °C average ambient temperature(1)	Blocks with 0–1000 P/E cycles	20	—	years
				Blocks with 10000 P/E cycles	10	—	years
				Blocks with 100000 P/E cycles	5	—	years

1. Ambient temperature averaged over duration of application, not to exceed recommended product operating temperature range.

ECC circuitry provides correction of single bit faults and is used to improve further automotive reliability results. Some units will experience single bit corrections throughout the life of the product with no impact to product reliability.

Table 29. Flash memory read access timing(1)

Symbol		C	Parameter	Conditions(2)		Frequency range	Unit
				Code flash memory	Data flash memory		
f_{READ}	CC	P	Maximum frequency for Flash reading	5 wait states	13 wait states	120 —100	MHz
		C		4 wait states	11 wait states	100—80	
		D		3 wait states	9 wait states	80—64	
		C		2 wait states	7 wait states	64—40	
		C		1 wait states	4 wait states	40—20	
		C		0 wait states	2 wait states	20—0	

1. Max speed is the maximum speed allowed including PLL frequency modulation (FM).
2. V_{DD} = 3.3 V ± 10 % / 5.0 V ± 10 %, T_A = –40 to 125 °C, unless otherwise specified.

3.10.2 Flash memory power supply DC characteristics

Table 30 shows the flash memory power supply DC characteristics on external supply.

Table 30. Flash memory power supply DC electrical characteristics

Symbol		Parameter	Conditions(1)		Value(2)			Unit
					Min	Typ	Max	
I_{CFREAD}(3)	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ on read access	Flash memory module read f_{CPU} = 120 MHz + 2%(4)	Code flash memory			33	mA
I_{DFREAD}(3)				Data flash memory			13	
I_{CFMOD}(3)	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ (program/erase)	Program/Erase on-going while reading flash memory registers f_{CPU} = 120 MHz + 2% (4)	Code flash memory			52	mA
I_{DFMOD}(3)				Data flash memory			13	
I_{CFLPW}(3)	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ during flash memory low power mode		Code flash memory			1.1	mA
I_{CFPWD}(3)	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ during flash memory power down mode		Code flash memory			150	µA
I_{DFPWD}(3)				Data flash memory			150	

1. V_{DD} = 3.3 V ± 10 % / 5.0 V ± 10 %, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. Data based on characterization results, not tested in production.
4. f_{CPU} 120 MHz + 2 % can be achieved over full temperature 125 °C ambient, 150 °C junction temperature.

3.11.2 Electromagnetic interference (EMI)

The product is monitored in terms of emission based on a typical application. This emission test conforms to the IEC61967-1 standard, which specifies the general conditions for EMI measurements.

Table 32. EMI radiated emission measurement(1)(2)

Symbol		C	Parameter	Conditions		Value			Unit
						Min	Typ	Max	
—	SR	—	Scan range	—		0.150		1000	MHz
f_{CPU}	SR	—	Operating frequency	—		—	120	—	MHz
V_{DD_LV}	SR	—	LV operating voltages	—		—	1.28	—	V
S_{EMI}	CC	T	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP176 package Test conforming to IEC 61967-2, f_{OSC} = 40 MHz/f_{CPU} = 120 MHz	No PLL frequency modulation	—	—	18	dBµV
					± 2% PLL frequency modulation	—	—	14(3)	dBµV

1. EMI testing and I/O port waveforms per IEC 61967-1, -2, -4.
2. For information on conducted emission and susceptibility measurement (norm IEC 61967-4), please contact your local marketing representative.
3. All values need to be confirmed during device validation.

3.11.3 Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity.

3.11.3.1 Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pin). This test conforms to the AEC-Q100-002/-003/-011 standard. For more details, refer to the application note *Electrostatic Discharge Sensitivity Measurement* (AN1181).

Table 33. ESD absolute maximum ratings(1)(2)

Symbol	Ratings	Conditions	Class	Max value(3)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	T_A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)	T_A = 25 °C conforming to AEC-Q100-003	M2	200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charged Device Model)	T_A = 25 °C conforming to AEC-Q100-011	C3A	500	
				750 (corners)	

1. All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.
2. A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.
3. Data based on characterization results, not tested in production.

3.11.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply over-voltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

Table 34. Latch-up results

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = 125 °C conforming to JESD 78	II level A

3.12 Fast external crystal oscillator (4–40 MHz) electrical characteristics

The device provides an oscillator/resonator driver. *Figure 10* describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

Table 35 provides the parameter description of 4 MHz to 40 MHz crystals used for the design simulations.

Figure 14. Slow external crystal oscillator (32 kHz) electrical characteristics

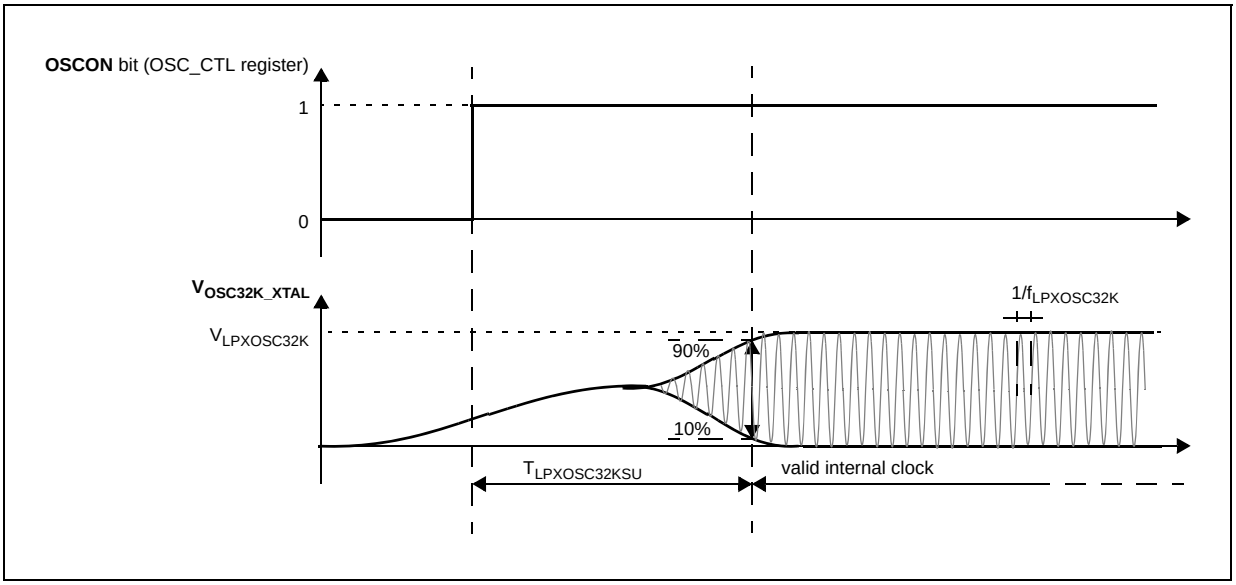
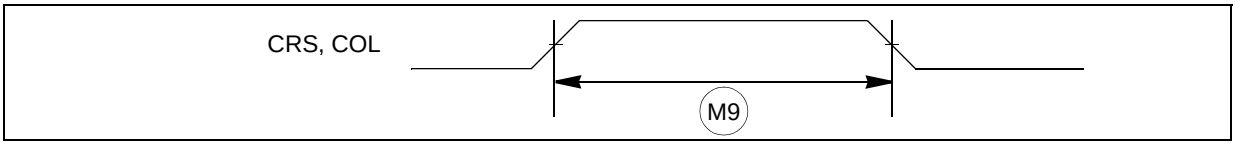


Table 38. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
f_{SXOSC}	SR	—	Slow external crystal oscillator frequency	—	32	32.768	40	kHz
g_{mSXOSC}	CC	—	Slow external crystal oscillator transconductance	V_{DD} = 3.3 V ± 10%,	13[3]	—	33[3]	µA/V
				V_{DD} = 5.0 V ± 10%	15[3]	—	35[3]	
V_{SXOSC}	CC	T	Oscillation amplitude	—	1.2	1.4	1.7	V
$I_{SXOSCBIAS}$	CC	T	Oscillation bias current	—	1.2	—	4.4	µA
I_{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	—	7	µA
$T_{SXOSCSU}$	CC	T	Slow external crystal oscillator start-up time	—	—	—	2[4]	s

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. All values need to be confirmed during device validation.
3. Based on ATE CZ
4. Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

Figure 23. MII async inputs timing diagram



3.18.4 MII Serial Management Channel Timing (MDIO and MDC)

The FEC functions correctly with a maximum MDC frequency of 2.5 MHz.

Table 48. MII serial management channel timing(1)

Spec	Characteristic	Min	Max	Unit
M10	MDC falling edge to MDIO output invalid (minimum propagation delay)	0	—	ns
M11	MDC falling edge to MDIO output valid (max prop delay)	—	25	ns
M12	MDIO (input) to MDC rising edge setup	28	—	ns
M13	MDIO (input) to MDC rising edge hold	0	—	ns
M14	MDC pulse width high	40%	60%	MDC period
M15	MDC pulse width low	40%	60%	MDC period

1. Output pads configured with SRE = 0b11.

Figure 24. MII serial management channel timing diagram

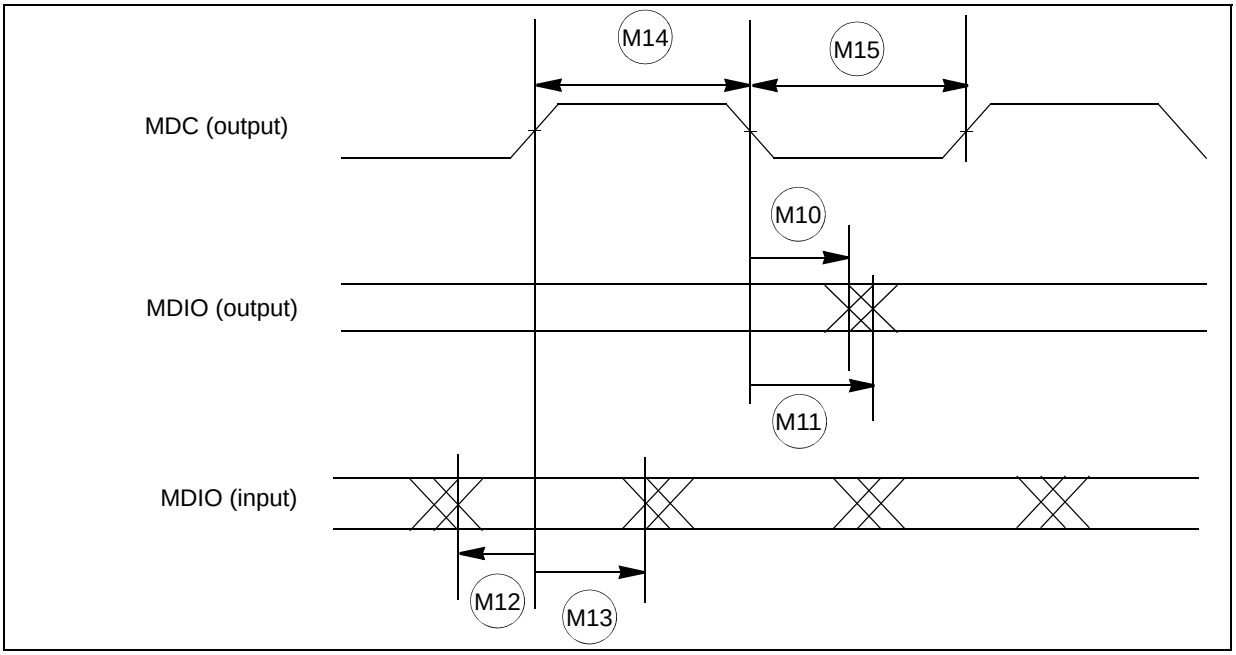


Table 50. DSPI timing (continued)

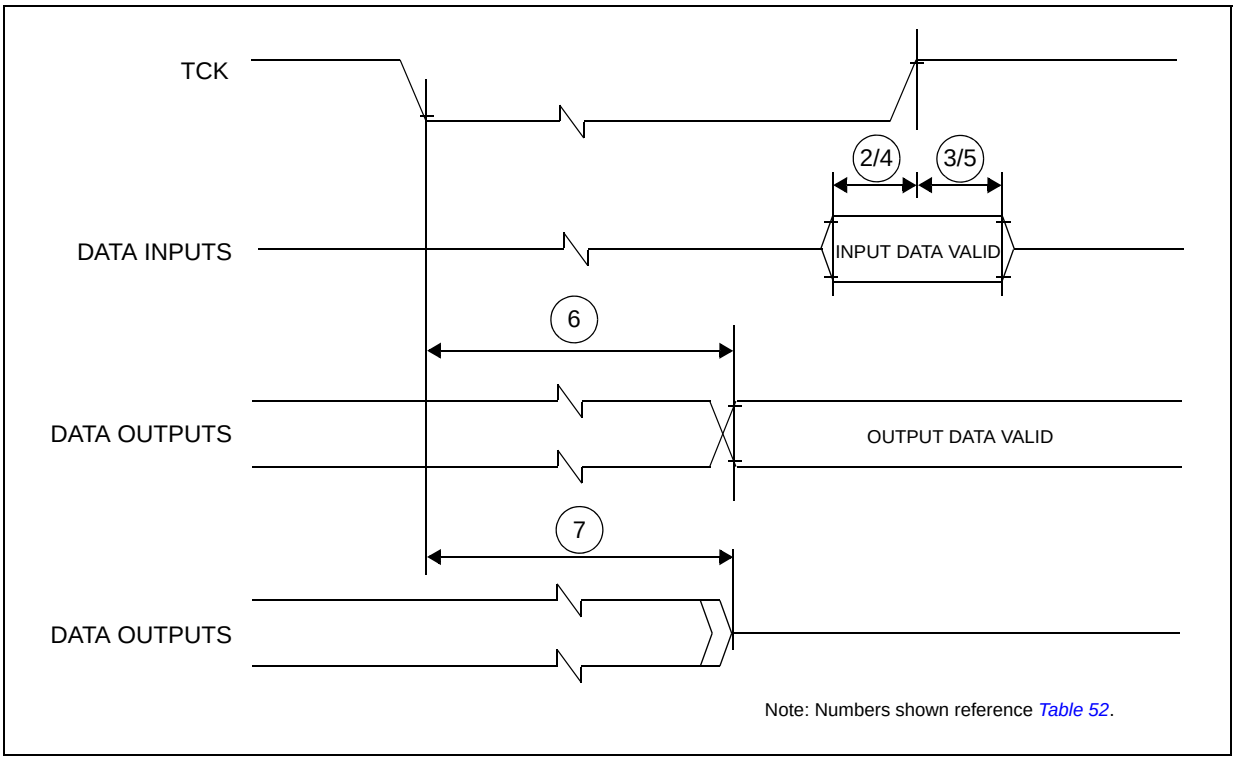
Spec	Characteristic	Symbol	Value		Unit
			Min	Max	
—	Slave Setup Time ($\overline{SS}$ active to SCK setup time)	t_{SUSS}	5	—	ns
—	Slave Hold Time ($\overline{SS}$ active to SCK hold time)	t_{HSS}	10	—	ns
5	Slave Access Time ($\overline{SS}$ active to SOUT valid)(4)	t_A	—	42	ns
6	Slave SOUT Disable Time ($\overline{SS}$ inactive to SOUT High-Z or invalid)	t_{DIS}	—	25	ns
7	CSx to $\overline{PCSS}$ time	t_{PCSC}	0	—	ns
8	$\overline{PCSS}$ to PCSx time	t_{PASC}	0	—	ns
9	Data Setup Time for Inputs Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = 0)(5) Master (MTFE = 1, CPHA = 1)	t_{SUI}	 36 5 36 36	 — — — —	 ns ns ns ns
10	Data Hold Time for Inputs Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = 0)(5) Master (MTFE = 1, CPHA = 1)	t_{HI}	 0 4 0 0	 — — — —	 ns ns ns ns
11	Data Valid (after SCK edge) Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = 0) Master (MTFE = 1, CPHA = 1)	t_{SUO}	 — — — —	 12 37 12 12	 ns ns ns ns
12	Data Hold Time for Outputs Master (MTFE = 0) Slave Master (MTFE = 1, CPHA = 0) Master (MTFE = 1, CPHA = 1)	t_{HO}	 0(6) 9.5 0(7) 0(8)	 — — — —	 ns ns ns ns

1. This value of this parameter is dependent upon the external device delays and the other parameters mentioned in this table.
2. The maximum value is programmable in DSPI_CTAR*n* [PSSCK] and DSPI_CTAR*n* [CSSCK]. For SPC564B74 and SPC56EC74, the spec value of t_{CSC} will be attained only if T_{DSPI} x PSSCK x CSSCK > Δt_{CSC}.
3. The maximum value is programmable in DSPI_CTAR*n* [PASC] and DSPI_CTAR*n* [ASC]. For SPC564B74 and SPC56EC74, the spec value of t_{ASC} will be attained only if T_{DSPI} x PASC x ASC > Δt_{ASC}.
4. The parameter value is obtained from t_{SUSS} and t_{SUO} for slave.
5. This number is calculated assuming the SMPL_PT bitfield in DSPI_MCR is set to 0b00.
6. For DSPI1, the Data Hold Time for Outputs in Master (MTFE = 0) is –2 ns.
7. For DSPI1, the Data Hold Time for Outputs in Master (MTFE = 1, CPHA = 0) is –2 n.
8. For DSPI1, the Data Hold Time for Outputs in Master (MTFE = 1, CPHA = 1) is –2 ns.

Table 52. JTAG characteristics (continued)

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
7	t_{TDOI}	CC	D	TCK low to TDO invalid	6	—	—	ns
—	t_{TDC}	CC	D	TCK Duty Cycle	40	—	60	%
—	$t_{TCKRISE}$	CC	D	TCK Rise and Fall Times	—	—	3	ns

Figure 36. Timing diagram - JTAG boundary scan



Note: Numbers shown reference *Table 52*.

Table 53. LQFP176 mechanical data[1]

Symbol	mm			inches[2]		
	Min	Typ	Max	Min	Typ	Max
A	1.400		1.600			0.063
A1	0.050		0.150	0.002		
A2	1.350		1.450	0.053		0.057
b	0.170		0.270	0.007		0.011
C	0.090		0.200	0.004		0.008
D	23.900		24.100	0.941		0.949
E	23.900		24.100	0.941		0.949
e		0.500			0.020	
HD	25.900		26.100	1.020		1.028
HE	25.900		26.100	1.020		1.028
L[3]	0.450		0.750	0.018		0.030
L1		1.000			0.039	
ZD		1.250			0.049	
ZE		1.250			0.049	
q	0 °		7 °	0 °		7 °
Tolerance	mm			inches		
ccc	0.080			0.0031		

1. Controlling dimension: millimeter.
2. Values in inches are converted from mm and rounded to 4 decimal digits.
3. L dimension is measured at gauge plane at 0.25 mm above the seating plane.